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# **EMH2308**



# P-Channel Power MOSFET –20V, –3A, 85mΩ, Dual EMH8

http://onsemi.com

### **Features**

- The EMH2308 incorporates a P-channel MOSFET that feature low ON-resistance and ultrahigh-speed switching, thereby enabling high-density mounting
- 1.8V drive
- · Halogen free compliance
- · Protection diode in

### **Specifications**

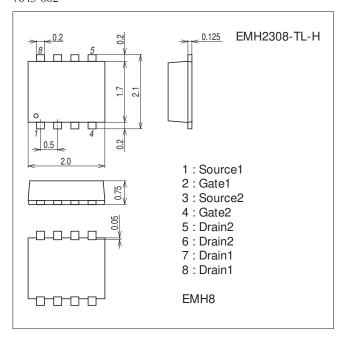
### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		-20	V
Gate-to-Source Voltage	VGSS		±10	V
Drain Current (DC)	ID		-3	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-20	Α
Allowable Power Dissipation	PD	When mounted on ceramic substrate (900mm <sup>2</sup> x0.8mm) 1unit	1.0	W
Total Dissipation	PT	When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm)	1.2	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

### **Package Dimensions**

unit : mm (typ) 7045-002



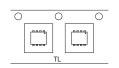
### **Product & Package Information**

Package : EMH8JEITA, JEDEC : -

JEIIII, JEDEC

• Minimum Packing Quantity : 3,000 pcs./reel

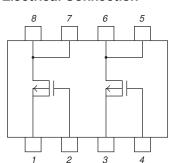
### Packing Type: TL



### Marking



### **Electrical Connection**

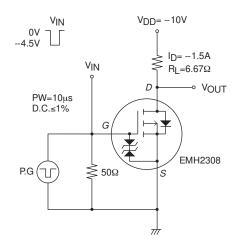


### **EMH2308**

### Electrical Characteristics at Ta=25°C

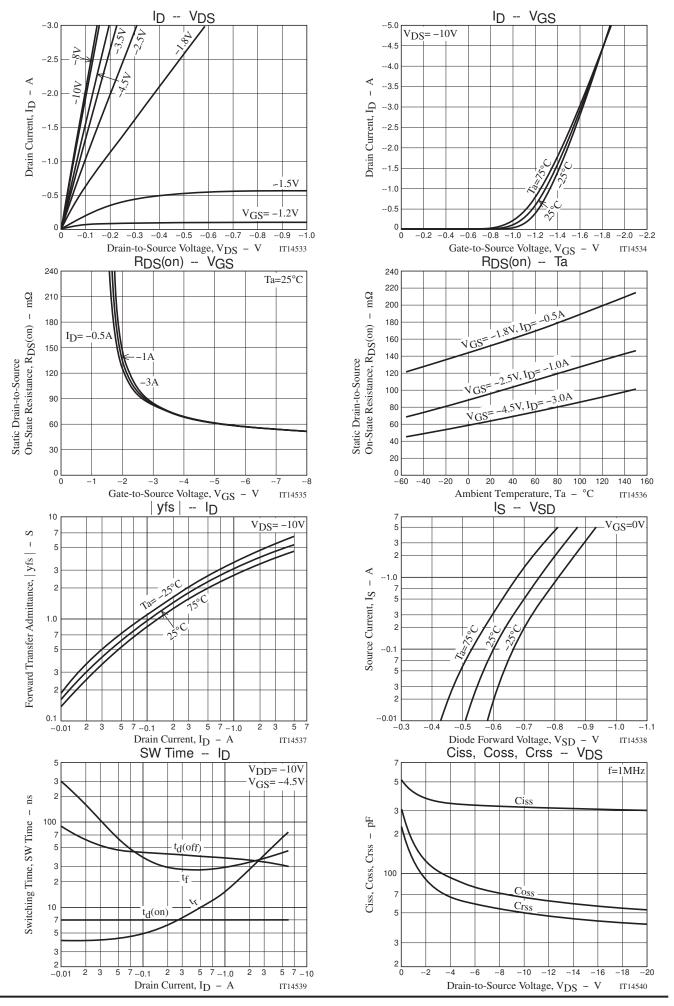
Parameter	Cumbal	Conditions	Ratings			Unit	
Parameter	Symbol	Conditions	min	typ	max	Onit	
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-20			V	
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V			-1	μΑ	
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μΑ	
Cutoff Voltage	VGS(off)	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-0.4		-1.3	V	
Forward Transfer Admittance	yfs	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1.5A	2.1	3.6		S	
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =-3A, V <sub>G</sub> S=-4.5V		65	85	mΩ	
	R <sub>DS</sub> (on)2	I <sub>D</sub> =-1.0A, V <sub>G</sub> S=-2.5V		98	137	mΩ	
	R <sub>DS</sub> (on)3	I <sub>D</sub> =-0.5A, V <sub>G</sub> S=-1.8V		155	235	mΩ	
Input Capacitance	Ciss			320		pF	
Output Capacitance	Coss	V <sub>DS</sub> =-10V, f=1MHz		66		pF	
Reverse Transfer Capacitance	Crss			50		pF	
Turn-ON Delay Time	t <sub>d</sub> (on)			7.1		ns	
Rise Time	t <sub>r</sub>	0 " 17 10"		21		ns	
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		37		ns	
Fall Time	tf			32		ns	
Total Gate Charge	Qg			4.0		nC	
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =-10V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-3A		0.6		nC	
Gate-to-Drain "Miller" Charge	Qgd	1		1.1		nC	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-3A, V <sub>GS</sub> =0V		-0.83	-1.2	V	

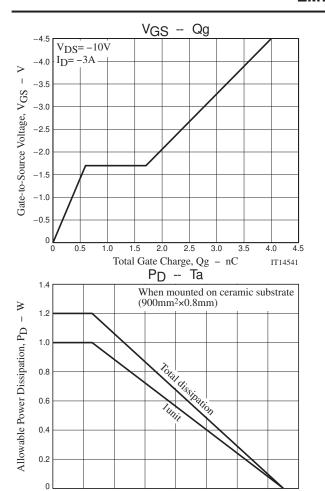
### **Switching Time Test Circuit**



### **Ordering Information**

Device	Package	Shipping	memo	
EMH2308-TL-H	H2308-TL-H EMH8		Pb Free and Halogen Free	





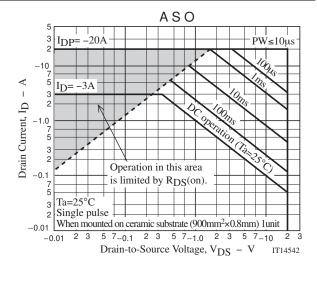
40 60 80 100 120 Ambient Temperature, Ta - °C

160

140 IT14543

20

0

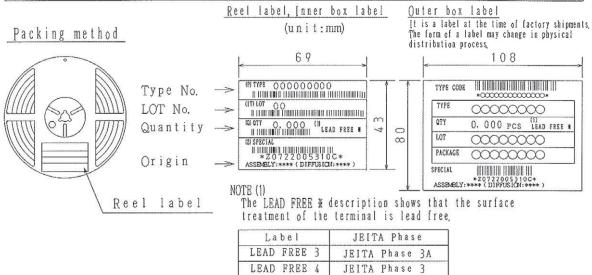


### **Embossed Taping Specification**

EMH2308-TL-H

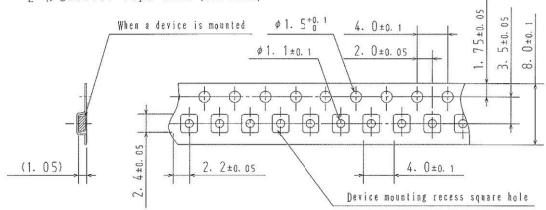
### 1. Packing Format

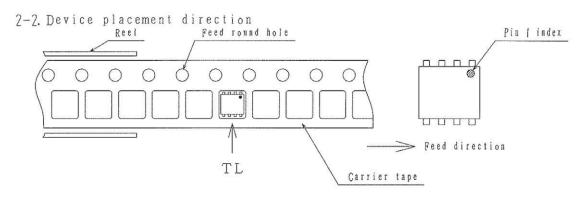
Package Name   Carrie	Carrier Tape	Maximum Number of devices contained (pcs)			Packing format		
	Type	Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)	
EMH8	MCP4	3, 000	15, 000	90, 000	S reels contained	6 inner boxes contained	
				5 July 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2	Dinensions:mm (external)	Dimensions:mm (external)	
					183×72×185	440×195×210	



### 2. Taping configuration

7-1. Carrier tape size (unit:mm)





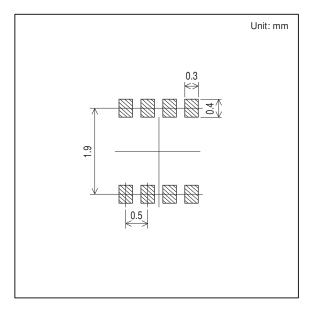
Those with pin 1 index on the feed hole side·····TL

### **Outline Drawing**

EMH2308-TL-H

# Mass (g) Unit 0.008 mm 2. 0±0.04 8 7 6 5 10 175-0.05

### **Land Pattern Example**



Note on usage: Since the EMH2308 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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